Svetlana Gudina

List of Publications by Year
in descending order

48	258	1307594 7	996975 15
papers	citations	h-index	g-index

49	49	49	192
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Rashba Spin Splitting in HgCdTe Quantum Wells with Inverted and Normal Band Structures. Nanomaterials, 2022, 12, 1238.	4.1	2
2	Anomalous phase shift of magneto-oscillations in HgTe quantum well with inverted energy spectrum. Journal of Magnetism and Magnetic Materials, 2021, 524, 167655.	2.3	1
3	Quasiclassical calculations of Landau level spectrum for 20.5-nm-wide H gTe quantum well: â€œextremum loopâ€•model and effects of cubic symmetry. Low Temperature Physics, 2021, 47, 7-13.	0.6	0
4	Localization and interference induced quantum effects at low magnetic fields in InGaAs/GaAs structures. Low Temperature Physics, 2021, 47, 14-18.	0.6	0
5	Effective Mass and g-Factor of Two-Dimentional HgTe Î“8-Band Electrons: Shubnikov-de Haas Oscillations. Semiconductors, 2020, 54, 982-990.	0.5	2
6	Determination of the magnetocaloric effect from thermophysical parameters and their relationships near magnetic phase transition in doped manganites. Journal of Magnetism and Magnetic Materials, 2020, 513, 167209.	2.3	7
7	Quantum Hall transitions in the presence of Landau levels mixing in n-InGaAs/InAlAs structures. IOP Conference Series: Materials Science and Engineering, 2019, 475, 012029.	0.6	0
8	Effect of exchange electron-electron interaction on conductivity of InGaAs single and double quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2019, 113, 14-20.	2.7	1
9	HgTe quantum wells with inverted band structure: Quantum Hall effect and the large-scale impurity potential. Low Temperature Physics, 2019, 45, 412-418.	0.6	4
10	Scaling laws under quantum Hall effect for a smooth disorder potential. Low Temperature Physics, 2019, 45, 176-180.	0.6	1
11	On the issue of universality of critical exponents in the quantum Hall effect mode. Low Temperature Physics, 2019, 45, 181-188.	0.6	2
12	â€œExtremum Loopâ€•Model for the Valence-Band Spectrum of a HgTe/HgCdTe Quantum Well with an Inverted Band Structure in the Semimetallic Phase. Semiconductors, 2018, 52, 1403-1406.	0.5	3
13	Nonuniversal Scaling Behavior of Conductivity Peak Widths in the Quantum Hall Effect in InGaAs/InAlAs Structures. Semiconductors, 2018, 52, 1551-1558.	0.5	2
14	Electron Effective Mass and g Factor in Wide HgTe Quantum Wells. Semiconductors, 2018, 52, 12-18.	0.5	4
15	Quantum Hall effect in n-InGaAs/InAlAs metamorphic nanoheterostructures with high InAs content. Journal of Magnetism and Magnetic Materials, 2017, 440, 10-12.	2.3	3
16	The temperature dependence of the conductivity peak values in the single and the double quantum well nanostructures n-InGaAs/GaAs after IR-illumination. Semiconductors, 2017, 51, 272-278.	0.5	1
17	Conditions for experimental observation of the critical behavior of the longitudinal and Hall resistance in the quantum Hall regime in gallium and indium arsenide-based heterostructures. Low Temperature Physics, 2017, 43, 478-484.	0.6	0
18	Activation transport under quantum Hall regime in HgTe-based heterostructure. Low Temperature Physics, 2017, 43, 485-490.	0.6	3

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19	Insulator-quantum Hall transition in n-InGaAs/GaAs heterostructures. Low Temperature Physics, 2017, 43, 491-494.	0.6	2
20	Antisymmetric contribution to the magnetoresistance of heterostructures in a parallel magnetic field. Low Temperature Physics, 2017, 43, 495-498.	0.6	0
21	Quantum Hall effect and hopping conductivity in n-InGaAs/InAlAs nanoheterostructures. Semiconductors, 2016, 50, 1641-1646.	0.5	2
22	2Dâ€localization and delocalization effects in quantum Hall regime in HgTe wide quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 473-476.	0.8	4
23	Variable-Range Hopping Conductivity in Quantum Hall Regime for HgTe-Based Heterostructure. Journal of Low Temperature Physics, 2016, 185, 665-672.	1.4	6
24	Quantum magnetotransport inn-InGaAs/GaAs structures with electron density changes caused by infrared radiation. Low Temperature Physics, 2015, 41, 221-232.	0.6	4
25	Temperature scaling in the quantum-Hall-effect regime in a HgTe quantum well with an inverted energy spectrum. Semiconductors, 2015, 49, 1545-1549.	0.5	11
26	Electron-electron interaction and the universality of critical indices for quantum Hall effect plateau-plateau transitions in n-InGaAs/GaAs nanostructures with double quantum wells. Semiconductors, 2015, 49, 181-186.	0.5	1
27	Quantum Hall plateau-plateau transitions inn-InGaAs/GaAs heterostructures before and after IR illumination. Low Temperature Physics, 2015, 41, 106-111.	0.6	6
28	Evolution of the energy structure of n-InGaAs/GaAs double quantum wells in tilted magnetic fields. Bulletin of the Russian Academy of Sciences: Physics, 2014, 78, 927-931.	0.6	1
29	Scaling in the Quantum Hall Regime for a Double Quantum Well Nanostructure in High Magnetic Field. Solid State Phenomena, 2014, 215, 208-213.	0.3	0
30	Scaling in the quantum Hall effect regime in n-InGaAs/GaAs nanostructures. Journal of Experimental and Theoretical Physics, 2013, 117, 144-152.	0.9	8
31	Temperature dependence of quantum lifetime inn-InGaAs/GaAs structures with strongly coupled double quantum wells. Low Temperature Physics, 2013, 39, 43-49.	0.6	5
32	Tunneling effects in tilted magnetic fields in n-InGaAs/GaAs structures with strongly coupled double quantum wells. Semiconductors, 2013, 47, 1447-1451.	0.5	1
33	The effect of infrared radiation on quantum magnetotransport in n-InGaAs/GaAs with two strongly coupled quantum wells. Low Temperature Physics, 2013, 39, 374-377.	0.6	6
34	Temperature dependence of the bandwidth of delocalized states for n-InGaAs/GaAs in the quantum Hall effect regime. Low Temperature Physics, 2013, 39, 50-57.	0.6	2
35	Contributions of the electronâ€“electron interaction and weak localization to the conductance of pâ€Geâˆ•Ge1âˆ’xSix heterostructures. Low Temperature Physics, 2007, 33, 160-164.	0.6	6
36	TRANSPORT PROPERTIES OF 2D ELECTRON GAS IN AN n-InGaAs/GaAs DQW IN A VICINITY OF LOW MAGNETIC-FIELD-INDUCED HALL INSULATORâ€“QUANTUM HALL LIQUID TRANSITION. International Journal of Nanoscience, 2007, 06, 173-177.	0.7	0

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37	Features of quantum effects in two-dimensional GaAsâˆ•nâ€InGaAsâˆ•GaAs structures with double quantum wells. Low Temperature Physics, 2007, 33, 156-159.	0.6	6
38	Transport Properties of 2D-Electron Gas in a InGaAs/GaAs DQW in a Vicinity of Low Magnetic-Field-Induced Insulator-Quantum Hall Liquid Transition. AIP Conference Proceedings, 2007, , .	0.4	2
39	Transport properties of two-dimensional hole gas in a Ge1âˆ’x Si x /Ge/Ge1âˆ’x Si x quantum well in the vicinity of metal-insulator transition. Semiconductors, 2007, 41, 1315-1322.	0.5	1
40	Thermoelectric properties of Czochralski-grown silicon at high pressure up to 16ÂGPa. EPJ Applied Physics, 2004, 27, 145-148.	0.7	7
41	Application of the high-pressure thermoelectric technique for characterization of semiconductor microsamples: PbX-based compounds. Journal Physics D: Applied Physics, 2004, 37, 1151-1157.	2.8	54
42	Czochralski silicon characterization by using thermoelectric power measurements at high pressure. Physica B: Condensed Matter, 2003, 340-342, 1026-1030.	2.7	8
43	Semiconductorâ€“metal transitions in lead chalcogenides at high pressure. Physica Status Solidi (B): Basic Research, 2003, 235, 521-525.	1.5	53
44	Thermoelectric properties of silicon at high pressures in the region of the semiconductor-metal transition. Technical Physics Letters, 2003, 29, 598-601.	0.7	9
45	Electrical properties of the high-pressure phases of gallium and indium tellurides. Physics of the Solid State, 2000, 42, 1036-1040.	0.6	11
46	Electrical properties of (PbS)0.59TiS2 crystals at high pressure up to 20 GPa. Physics of the Solid State, 2000, 42, 1228-1230.	0.6	3
47	Electrical properties of (PBS)0Â·59TiS2 crystals at high pressures up to 20GPa. High Pressure Research, 2000, 17, 347-353.	1.2	3
48	Quantum oscillations of magnetoresistance in HgCdTe/HgTe/HgCdTe heterostructures with inverted band spectrum. Physics of the Solid State, 0, , .	0.6	0